

Michael Jetter

List of Publications by Year in descending order

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220
papers

3,602
citations

126708

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182168

51
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229
all docs

229
docs citations

229
times ranked

3109
citing authors

#	ARTICLE	IF	CITATIONS
19	Mid-Infrared Spectroscopy Platform Based on GaAs/AlGaAs Thin-Film Waveguides and Quantum Cascade Lasers. <i>Analytical Chemistry</i> , 2016, 88, 2558-2562.	3.2	48
20	Coherence and indistinguishability of highly pure single photons from non-resonantly and resonantly excited telecom C-band quantum dots. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	48
21	InAs quantum dots grown on metamorphic buffers as non-classical light sources at telecom C-band: a review. <i>Semiconductor Science and Technology</i> , 2019, 34, 053001.	1.0	47
22	Semiconductor Quantum Dots for Integrated Quantum Photonics. <i>Advanced Quantum Technologies</i> , 2019, 2, 1900020.	1.8	45
23	Simultaneous Faraday filtering of the Mollow triplet sidebands with the Cs-D1 clock transition. <i>Nature Communications</i> , 2016, 7, 13632.	5.8	43
24	Near-red emission from site-controlled pyramidal InGaN quantum dots. <i>Applied Physics Letters</i> , 2005, 87, 163121.	1.5	41
25	Structural and optical properties of InAs/(In)GaAs/GaAs quantum dots with single-photon emission in the telecom C-band up to 77 K. <i>Physical Review B</i> , 2018, 98, .	1.1	41
26	Influence of the Dark Exciton State on the Optical and Quantum Optical Properties of Single Quantum Dots. <i>Physical Review Letters</i> , 2008, 101, 146402.	2.9	40
27	Bright Purcell Enhanced Single-Photon Source in the Telecom O-Band Based on a Quantum Dot in a Circular Bragg Grating. <i>Nano Letters</i> , 2021, 21, 7740-7745.	4.5	39
28	Electrically pumped single-photon emission in the visible spectral range up to 80 K. <i>Optics Express</i> , 2008, 16, 12771.	1.7	38
29	Reducing vortex losses in superconducting microwave resonators with microsphere patterned antidot arrays. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	38
30	Monolithic on-chip integration of semiconductor waveguides, beamsplitters and single-photon sources. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 085101.	1.3	36
31	Metal-organic vapor-phase epitaxy-grown ultra-low density InGaAs/GaAs quantum dots exhibiting cascaded single-photon emission at 1.3 μm . <i>Applied Physics Letters</i> , 2015, 106, .	1.5	36
32	Mode-locked red-emitting semiconductor disk laser with sub-250 fs pulses. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	35
33	Deterministic integration and optical characterization of telecom O-band quantum dots embedded into wet-chemically etched Gaussian-shaped microlenses. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	33
34	Electronic shell structure and carrier dynamics of high aspect ratio InP single quantum dots. <i>Physical Review B</i> , 2007, 75, .	1.1	31
35	Quantitative measurements of internal electric fields with differential phase contrast microscopy on InGaN/GaN quantum well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 140-144.	0.7	31
36	On-chip beamsplitter operation on single photons from quasi-resonantly excited quantum dots embedded in GaAs rib waveguides. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	30

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37	Generation, guiding and splitting of triggered single photons from a resonantly excited quantum dot in a photonic circuit. <i>Optics Express</i> , 2016, 24, 3089.	1.7	30
38	Two-photon interference in an atom-quantum dot hybrid system. <i>Optica</i> , 2018, 5, 367.	4.8	29
39	Single-photon emission from a type-B InP-GaN quantum dot. <i>Journal of Applied Physics</i> , 2005, 98, 093522.	1.1	27
40	Triggered single-photon emission from electrically excited quantum dots in the red spectral range. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	27
41	Low-noise quantum frequency down-conversion of indistinguishable photons. <i>Optics Express</i> , 2016, 24, 22250.	1.7	27
42	Deterministic fabrication of circular Bragg gratings coupled to single quantum emitters via the combination of <i>in-situ</i> optical lithography and electron-beam lithography. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	27
43	3D printed micro-optics for quantum technology: Optimised coupling of single quantum dot emission into a single-mode fibre. <i>Light Advanced Manufacturing</i> , 2021, 2, 103.	2.2	26
44	Red to green photoluminescence of InP-quantum dots in InP. <i>Journal of Crystal Growth</i> , 2007, 298, 595-598.	0.7	25
45	Short wavelength red-emitting AlGaInP-VECSEL exceeds 1.2-W continuous-wave output power. <i>Applied Physics B: Lasers and Optics</i> , 2011, 102, 789-794.	1.1	25
46	High-power InP quantum dot based semiconductor disk laser exceeding 1.3-W. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	25
47		1.1	24
48	25-W continuous wave output at 665-nm from a multipass and quantum-well-pumped AlGaInP vertical-external-cavity surface-emitting laser. <i>Optics Letters</i> , 2016, 41, 1245.	1.7	24
49	Room-temperature lasing of electrically pumped red-emitting InP/(Al _{0.20} Ga _{0.80}) _{0.51} In _{0.49} P quantum dots embedded in a vertical microcavity. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	23
50	DBR-free semiconductor disc laser on SiC heatspreader emitting 10.1 W at 1007-nm. <i>Electronics Letters</i> , 2017, 53, 1537-1539.	0.5	23
51	Wavelength tunable ultraviolet laser emission via intra-cavity frequency doubling of an AlGaInP vertical external-cavity surface-emitting laser down to 328-nm. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	22
52	Intra-cavity frequency-doubled mode-locked semiconductor disk laser at 325 nm. <i>Optics Express</i> , 2015, 23, 19947.	1.7	22
53	High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 605-610.	0.7	21
54	Spectroscopy of the of cesium by dressed-state resonance fluorescence from a single (In,Ga)As/GaAs quantum dot. <i>Physical Review B</i> , 2014, 90, .	1.1	21

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55	Neutral and charged biexciton-exciton cascade in near-telecom-wavelength quantum dots. Physical Review B, 2016, 94, .	1.1	21
56	Time- and locally resolved photoluminescence of semipolar GaInN ^x GaN facet light emitting diodes. Applied Physics Letters, 2007, 90, 171123.	1.5	20
57	Thin-film InGaAs metamorphic buffer for telecom C-band InAs quantum dots and optical resonators on GaAs platform. Nanophotonics, 2022, 11, 1109-1116.	2.9	20
58	Electric-Field Tuning of Spin-Dependent Exciton-Exciton Interactions in Coupled Quantum Wells. Physical Review Letters, 1999, 83, 2433-2436.	2.9	19
59	Structural and emission properties of InGaAs/GaAs quantum dots emitting at 1.3 μ m. Applied Physics Letters, 2014, 105, 152102.	1.5	19
60	High optical output power in the UVA range of a frequency-doubled, strain-compensated AlGaInP-VECSEL. Applied Physics Express, 2014, 7, 092705.	1.1	19
61	Resonance fluorescence of single In(Ga)As quantum dots emitting in the telecom C-band. Applied Physics Letters, 2021, 118, .	1.5	19
62	Optical charge injection and coherent control of a quantum-dot spin-qubit emitting at telecom wavelengths. Nature Communications, 2022, 13, 748.	5.8	19
63	Enhanced efficiency of AlGaInP disk laser by in-well pumping. Optics Express, 2015, 23, 2472.	1.7	18
64	Single-photon and photon pair emission from MOVPE-grown In(Ga)As quantum dots: shifting the emission wavelength from 1.0 to 1.3 μ m. Applied Physics B: Lasers and Optics, 2016, 122, 1.	1.1	18
65	Temperature-dependent properties of single long-wavelength InGaAs quantum dots embedded in a strain reducing layer. Journal of Applied Physics, 2017, 121, 184302.	1.1	18
66	Chem/bio sensing with non-classical light and integrated photonics. Analyst, The, 2018, 143, 593-605.	1.7	18
67	Triggered single-photon emission in the red spectral range from optically excited InP/(Al,Ga)InP quantum dots embedded in micropillars up to 100 K. Journal of Applied Physics, 2011, 110, 063108.	1.1	17
68	Optical Gain and Lasing Properties of InP/AlGaInP Quantum-Dot Laser Diode Emitting at 660 nm. IEEE Journal of Quantum Electronics, 2019, 55, 1-7.	1.0	17
69	Nonresonant tunneling in single asymmetric pairs of vertically stacked InP quantum dots. Physical Review B, 2007, 76, .	1.1	16
70	Mollow quintuplets from coherently excited quantum dots. Optics Letters, 2013, 38, 1691.	1.7	16
71	Purcell-enhanced single-photon emission from a strain-tunable quantum dot in a cavity-waveguide device. Applied Physics Letters, 2020, 117, .	1.5	16
72	Bragg grating cavities embedded into nano-photonic waveguides for Purcell enhanced quantum dot emission. Optics Express, 2018, 26, 30614.	1.7	16

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73	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser. Optics Express, 2019, 27, 11914.	1.7	16
74	Quantum dot-based broadband optical antenna for efficient extraction of single photons in the telecom O-band. Optics Express, 2020, 28, 19457.	1.7	16
75	Red VCSEL for high-temperature applications. Journal of Crystal Growth, 2004, 272, 549-554.	0.7	15
76	Postselected indistinguishable single-photon emission from the Mollow triplet sidebands of a resonantly excited quantum dot. Physical Review B, 2013, 87, .	1.1	15
77	Self-mode-locked AlGaInP-VECSEL. Applied Physics Letters, 2017, 111, .	1.5	15
78	Overcoming correlation fluctuations in two-photon interference experiments with differently bright and independently blinking remote quantum emitters. Physical Review B, 2018, 97, .	1.1	15
79	Low Threshold InP/AlGaInP Quantum Dot In-Plane Laser Emitting at 638 nm. Applied Physics Express, 2009, 2, 112501.	1.1	14
80	All quantum dot mode-locked semiconductor disk laser emitting at 655 nm. Applied Physics Letters, 2014, 105, .	1.5	14
81	Selective growth of GaInN quantum dot structures. Journal of Crystal Growth, 2004, 272, 204-210.	0.7	13
82	Characterisation of quaternary AlInGaN thick layers and quantum wells grown by MOVPE. Journal of Crystal Growth, 2004, 272, 386-392.	0.7	13
83	Red single-photon emission from an InP/GaInP quantum dot embedded in a planar monolithic microcavity. Applied Physics Letters, 2008, 92, .	1.5	13
84	Low-density InP quantum dots embedded in Ga _{0.51} In _{0.49} P with high optical quality realized by a strain inducing layer. Applied Physics Letters, 2010, 97, 063107.	1.5	13
85	Polarization fine structure and enhanced single-photon emission of self-assembled lateral InGaAs quantum dot molecules embedded in a planar microcavity. Journal of Applied Physics, 2009, 105, 122408.	1.1	12
86	Low density MOVPE grown InGaAs QDs exhibiting ultra-narrow single exciton linewidths. Nanotechnology, 2010, 21, 125606.	1.3	12
87	Spectrally and time-resolved cathodoluminescence microscopy of semipolar InGaN SQW on (11 $\bar{2}$) and (10 $\bar{1}$) pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 632-637.	0.7	12
88	Laterally Coupled InGaN/GaN DFB Laser Diodes. Physica Status Solidi A, 2002, 192, 301-307.	1.7	11
89	Electron and hole spins in InP/(Ga,In)P self-assembled quantum dots. Physical Review B, 2012, 86, .	1.1	10
90	Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). Nanotechnology, 2012, 23, 335201.	1.3	10

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91	Strain compensation techniques for red AlGaInP-VECSELs: Performance comparison of epitaxial designs. <i>Journal of Crystal Growth</i> , 2013, 370, 208-211.	0.7	10
92	Pure single-photon emission from In(Ga)As QDs in a tunable fiber-based external mirror microcavity. <i>Quantum Science and Technology</i> , 2018, 3, 034009.	2.6	10
93	Investigations on local Ga and In incorporation of GaInN quantum wells on facets of selectively grown GaN stripes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1587-1590.	0.8	9
94	Vertical asymmetric double quantum dots. <i>Journal of Crystal Growth</i> , 2007, 298, 603-606.	0.7	9
95	Transverse-Mode Analysis of Red-Emitting Highly Polarized Vertical-Cavity Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 724-729.	1.9	9
96	Quaternary Al _x In _y Ga _{1-x-y} N layers deposited by pulsed metal-organic vapor-phase epitaxy for high efficiency light emission. <i>Journal of Crystal Growth</i> , 2011, 315, 254-257.	0.7	9
97	Strong antibunching from electrically driven devices with long pulses: A regime for quantum-dot single-photon generation. <i>Physical Review B</i> , 2012, 86, .	1.1	9
98	Strong mode coupling in InP quantum dot-based GaInP microdisk cavity dimers. <i>New Journal of Physics</i> , 2013, 15, 013060.	1.2	9
99	Characterization of a Photon-Number Resolving SNSPD Using Poissonian and Sub-Poissonian Light. <i>IEEE Transactions on Applied Superconductivity</i> , 2019, 29, 1-5.	1.1	9
100	Characterization of spectral diffusion by slow-light photon-correlation spectroscopy. <i>Physical Review B</i> , 2020, 101, .	1.1	9
101	Evidence of different confinement regimes in site-controlled pyramidal InGaN structures. <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, R97-R99.	0.7	8
102	Excited-state spectroscopy of single lateral self-assembled InGaAs quantum dot molecules. <i>Physical Review B</i> , 2012, 85, .	1.1	8
103	Vertically stacked and laterally ordered InP and In(Ga)As quantum dots for quantum gate applications. <i>Physica Status Solidi (B): Basic Research</i> , 2012, 249, 737-746.	0.7	8
104	Comparison of AlGaInP-VECSEL gain structures. <i>Journal of Crystal Growth</i> , 2015, 414, 219-222.	0.7	8
105	Single-photon light-emitting diodes based on preselected quantum dots using a deterministic lithography technique. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	8
106	Achieving stable fiber coupling of quantum dot telecom C-band single-photons to an SOI photonic device. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	8
107	Integrated Optoelectronic Devices Using Lab-on-a-Fiber Technology. <i>Advanced Materials Technologies</i> , 2022, 7, .	3.0	8
108	Pulsed single-photon resonant-cavity quantum dot LED. <i>Journal of Crystal Growth</i> , 2011, 315, 127-130.	0.7	7

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109	Signatures of single-photon interaction between two quantum dots located in different cavities of a weakly coupled double microdisk structure. <i>Physical Review B</i> , 2018, 97, .	1.1	7
110	Tuning emission energy and fine structure splitting in quantum dots emitting in the telecom O-band. <i>AIP Advances</i> , 2019, 9, .	0.6	7
111	Time-resolved and single dot spectroscopy of type II InP/GaN quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1197-1200.	0.8	6
112	160Å°C pulsed laser operation of AlGaInP-based vertical-cavity surface-emitting lasers. <i>Electronics Letters</i> , 2003, 39, 1654.	0.5	6
113	Selective growth of GaInN quantum dot structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 26, 133-137.	1.3	6
114	Red to orange electroluminescence from InP/AlGaInP quantum dots at room temperature. <i>Journal of Crystal Growth</i> , 2008, 310, 5098-5101.	0.7	6
115	Optical studies of GaInP/GaP quantum dots. <i>Journal of Luminescence</i> , 2003, 102-103, 1-6.	1.5	5
116	Red VCSEL for automotive applications. , 2005, , .		5
117	Transport of laser accelerated proton beams and isochoric heating of matter. <i>Journal of Physics: Conference Series</i> , 2010, 244, 012009.	0.3	5
118	Optical properties of red emitting self-assembled InP/(Al _{0.20} Ga _{0.80}) _{0.51} In _{0.49} P quantum dot based micropillars. <i>Optics Express</i> , 2010, 18, 12543.	1.7	5
119	The phase boundary of superconducting niobium thin films with antidot arrays fabricated with microsphere photolithography. <i>Superconductor Science and Technology</i> , 2012, 25, 065020.	1.8	5
120	Optical investigations on single vertically coupled InP/GaN quantum dot pairs. <i>Physica Status Solidi (B): Basic Research</i> , 2012, 249, 747-751.	0.7	5
121	Controllable Delay and Polarization Routing of Single Photons. <i>Advanced Quantum Technologies</i> , 2020, 3, 1900057.	1.8	5
122	Stable fundamental and dual-pulse mode locking of red-emitting VCSELs. <i>Laser Physics Letters</i> , 2020, 17, 065001.	0.6	5
123	Realization of a tunable fiber-based double cavity system. <i>Physical Review B</i> , 2020, 102, .	1.1	5
124	In-Redistribution in a GaInN Quantum Well upon Thermal Annealing. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 234, 738-741.	0.7	4
125	Initial Experiments to Obtain Self-Assembled GaInN Quantum Islands by MOVPE. <i>Physica Status Solidi A</i> , 2002, 192, 412-416.	1.7	4
126	Increased single-photon emission from InP/AlGaInP quantum dots grown on AlGaAs distributed Bragg reflectors. <i>Journal of Crystal Growth</i> , 2008, 310, 4818-4820.	0.7	4

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127	Low threshold electrically pumped red emitting InP/Al _{0.20} GaNP quantum dot vertical microcavity laser. , 2009, , .		4
128	InP quantum dots for applications in laser devices and future solid-state quantum gates. Journal of Physics: Conference Series, 2010, 245, 012077.	0.3	4
129	Red AlGaInP-VECSEL emitting at around 665 nm: strain compensation and performance comparison of different epitaxial designs. Proceedings of SPIE, 2012, , .	0.8	4
130	Site-controlled growth of InP/GaN islands on periodic hole patterns in GaAs substrates produced by microsphere photolithography. Journal of Crystal Growth, 2013, 370, 146-149.	0.7	4
131	Optical studies of Ga _x In _{1-x} P/Ga _{0.5} In _{0.5} P quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1225-1228.	0.8	3
132	Regions of Different Confinement in Low-Dimensional Al _y In _x Ga _{1-x-y} N Quantum Structures. Advances in OptoElectronics, 2007, 2007, 1-6.	0.6	3
133	Wavelength tunable red AlGaInP-VECSEL emitting at around 660 nm. Proceedings of SPIE, 2011, , .	0.8	3
134	Growth and characterization of electrically pumped red-emitting VCSEL with embedded InP/AlGaInP quantumdots. Journal of Crystal Growth, 2011, 315, 131-133.	0.7	3
135	MOVPE grown quaternary AlInGaN layers for polarization matched quantum wells and efficient active regions. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2163-2166.	0.8	3
136	Influence of the oxide aperture radius on the mode spectra of (Al,Ga)As vertical microcavities with electrically excited InP quantum dots. Applied Physics Letters, 2013, 102, .	1.5	3
137	Active and Passive LC Based Polarization Elements. Molecular Crystals and Liquid Crystals, 2014, 594, 140-149.	0.4	3
138	Quantum dot based mode-locked AlGaInP-VECSEL. Proceedings of SPIE, 2015, , .	0.8	3
139	Gain chip design, power scaling and intra-cavity frequency doubling with LBO of optically pumped red-emitting AlGaInP-VECSELS. , 2016, , .		3
140	Semiconductor Quantum Dots for Integrated Quantum Photonics (Adv. Quantum Technol. 9/2019). Advanced Quantum Technologies, 2019, 2, 1970053.	1.8	3
141	Wavelength and Pump-Power Dependent Nonlinear Refraction and Absorption in a Semiconductor Disk Laser. IEEE Photonics Technology Letters, 2020, 32, 85-88.	1.3	3
142	Gaussian-like transverse-mode profile characteristics of high-power large-area red-emitting VCSELS. Optics Letters, 2020, 45, 1419.	1.7	3
143	High-power quasi-CW diode-pumped 750-nm AlGaAs VECSEL emitting a peak power of 29.6W and an average power of 8.5W. Optics Letters, 2022, 47, 1980.	1.7	3
144	Optical investigations on InP and GaInP quantum dots. , 0, , .		2

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145	Photoluminescence Studies on InGaN/GaN Quantum Dots. Physica Status Solidi A, 2002, 192, 91-96.	1.7	2
146	Analysis of the modulation behavior of red VCSELs. , 2004, 5597, 102.		2
147	Growth of self-assembled AlInGaN quantum dots by MOVPE. Journal of Crystal Growth, 2004, 272, 186-191.	0.7	2
148	Structural and optical characterization of $\text{Al}_y\text{In}_x\text{Ga}_{1-x-y}\text{N}$ quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2073-2077.	0.8	2
149	Pulsed layer growth of AlInGaN nanostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1491-1494.	0.8	2
150	Non-resonant tunneling in single pairs of vertically stacked asymmetric InP/GaN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1958-1960.	1.3	2
151	InP-quantum dots in $\text{Al}_{0.20}\text{Ga}_{0.80}\text{InP}$ with different barrier configurations. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 906-909.	0.8	2
152	InP quantum dots in pillar microcavities mode spectra and single-photon emission. Journal of Physics: Conference Series, 2010, 210, 012010.	0.3	2
153	Spectral features in different sized InGaN/GaN micropyramids. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2387-2389.	0.8	2
154	Generation of UV laser light via intra-cavity frequency doubling of an AlGaInP-VECSEL. , 2011, , .		2
155	Frequency doubled AlGaInP-VECSEL with high output power at 331 nm and a large wavelength tuning range in the UV. , 2012, , .		2
156	UV laser emission around 330 nm via intracavity frequency doubling of a tunable red AlGaInP-VECSEL. , 2012, , .		2
157	Epitaxially Grown Indium Phosphide Quantum Dots on a Virtual Ge Substrate Realized on Si(001). Applied Physics Express, 2012, 5, 042001.	1.1	2
158	Femtosecond mode-locked red AlGaInP-VECSEL. Proceedings of SPIE, 2014, , .	0.8	2
159	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 67-72.	0.7	2
160	Efficiency and power scaling of in-well and multi-pass pumped AlGaInP VECSELs. Proceedings of SPIE, 2016, , .	0.8	2
161	The optically pumped semiconductor membrane external-cavity surface-emitting laser (MECSEL): a concept based on a diamond-sandwiched active region. , 2017, , .		2
162	InGaAsP VECSEL for watt-level output at a wavelength around 765 nm. Optics Letters, 2022, 47, 2178.	1.7	2

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163	Red surface emitters: powerful and fast. , 2003, , .		1
164	Study of as deposited metal contacts for n-SiC. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2533-2536.	0.8	1
165	Analog Modulation of 650-nm VCSELs. IEEE Photonics Technology Letters, 2006, 18, 583-585.	1.3	1
166	Carrier dynamics in site-controlled Ga _{1-x} In _x N quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2060-2064.	0.8	1
167	Red high-temperature AlGaInP-VCSEL. , 2007, , .		1
168	Growth of red InP/GaInP quantum dots on a low density InAs/GaAs island seed layer by MOVPE. Journal of Crystal Growth, 2008, 310, 5089-5092.	0.7	1
169	DC and pulsed electrical excitation of single quantum dots. Proceedings of SPIE, 2010, , .	0.8	1
170	Transverse mode and polarization characteristics of AlGaInP-based VCSELs with integrated multiple oxide apertures. Proceedings of SPIE, 2012, , .	0.8	1
171	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839.	0.2	1
172	Fabrication and optical characterization of large scale membrane containing InP/AlGaInP quantum dots. Nanotechnology, 2015, 26, 235201.	1.3	1
173	Schemes for efficient QW pumping of AlGaInP disk lasers. Proceedings of SPIE, 2017, , .	0.8	1
174	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser: erratum. Optics Express, 2021, 29, 23290.	1.7	1
175	Single-photon and polarization-entangled photon emission from InAs quantum dots in the telecom C-band. , 2018, , .		1
176	Development of electrically pumped VECSEL in the visible spectrum. , 2019, , .		1
177	Subthreshold Spectral Bi-Modality of Double Layer InP/AlGaInP Quantum Dot Laser. , 2021, , .		1
178	Non-equilibrium spin noise spectroscopy of a single quantum dot operating at fiber telecommunication wavelengths. Journal of Applied Physics, 2022, 131, 065703.	1.1	1
179	Spin-Dependent Exciton-Exciton Interaction in Quantum Wells under an Electric Field. Physica Status Solidi (B): Basic Research, 1999, 215, 223-228.	0.7	0
180	Optically Induced Stark Shift in DFB Resonators. Physica Status Solidi (B): Basic Research, 1999, 215, 269-273.	0.7	0

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181	Comparison of the material properties of GaInN structures grown with ammonia and dimethyl-hydrazine as nitrogen precursors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2145-2149.	0.8	0
182	Red light VCSEL for high-temperature applications. , 2004, 5594, 141.		0
183	Technology transfer of (Ga)InP-quantum dots. , 0, , .		0
184	Temperature Dependent Photoluminescence Measurements of Single InP Quantum Dots. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	0
185	Green photoluminescence of single InP-quantum dots grown on InP/AlInP distributed Bragg reflectors. <i>Journal of Crystal Growth</i> , 2007, 298, 599-602.	0.7	0
186	Low threshold and room-temperature lasing of electrically pumped red-emitting InP/(Al _{0.20} Ga _{0.80}) _{0.51} In _{0.49} P quantum dots. <i>Journal of Physics: Conference Series</i> , 2010, 210, 012009.	0.3	0
187	MOVPE grown InGaAs quantum dots of high optical quality as seed layer for low-density InP quantum dots. <i>Journal of Physics: Conference Series</i> , 2010, 245, 012009.	0.3	0
188	Influence of the Exciton Dark State on the Optical and Quantum Optical Properties of Single Quantum Dots. , 2010, , .		0
189	Electrically pumped single-photon emission up to 80 K Towards a commercial single-photon emitting device. , 2010, , .		0
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